



70V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C	
-70V	160mΩ @ V _{GS} = -10V	-2.6A	
-70V	250mΩ @ V _{GS} = -4.5V	-1.6A	

Description

This MOSFET is designed to minimize on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Available (Note 4)

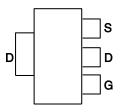
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

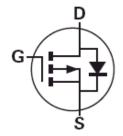
SOT223



Top View



Pin Out - Top



Equivalent Circuit

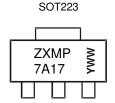
Ordering Information (Notes 4 & 5)

Part Number	Qualification	Case	Packaging
ZXMP7A17GQTA	Automotive	SOT223	1,000/Tape & Reel
ZXMP7A17GQTC	Automotive	SOT223	4,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
- $5.\ For\ packaging\ details,\ go\ to\ our\ website\ at\ http://www.diodes.com/products/packages.html.$

Marking Information



ZXMP7A17 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or \overline{W} W = Week Code (01~53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-70	V	
Gate-Source Voltage		V _{GS}	±20	V	
		(Note 7)		-3.7	
Continuous Drain Current	$V_{GS} = -10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	I _D	-2.9	Α
		(Note 6)		-2.6	
Pulsed Drain Current	V _{GS} = -10V	(Note 8)	I _{DM}	-9.6	Α
Continuous Source Current (Body Diode) (Note 7)		(Note 7)	I _S	-4.8	Α
Pulsed Source Current (Body Diode) (Note 8)		I _{SM}	-9.6	Α	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)		2 16	W mW/°C	
Linear Derating Factor	(Note 7)	P _D	3.9 31		
Thermal Resistance, Junction to Ambient	(Note 6) (Note 7)	R _{0JA}	62.5 34	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

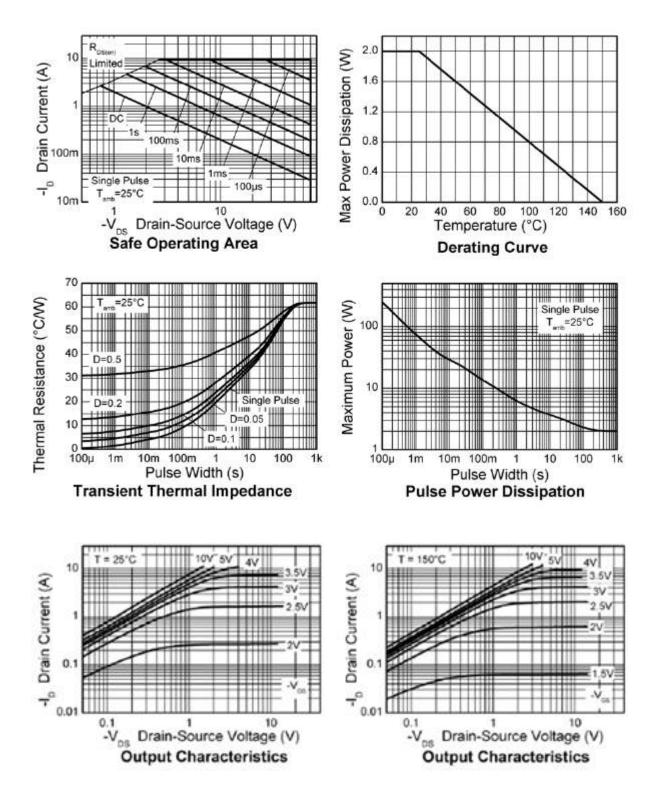
			_					
Characteristic	Symbol	Min	Тур	Max	Unit	Test C	Condition	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	-70		_	V	$I_D = -250 \mu A, V_{GS} = 0 V$		
Zero Gate Voltage Drain Current	I _{DSS}	_		-1	μΑ	V _{DS} = -70V, V _{GS}	= 0V	
Gate-Source Leakage	I _{GSS}			100	nA	$V_{GS} = \pm 20V, V_{DS}$	S= 0V	
ON CHARACTERISTICS								
Gate Threshold Voltage	V _{GS(th)}	-1	_	_	V	I _D = -250μA, V _D s	I _D = -250μA, V _D S= V _G S	
Static Drain-Source On-Resistance (Note 9)	J			0.16	Ω	V _{GS} = -10V, I _D = -2.1A		
Static Drain-Source On-Nesistance (Note 9)	R _{DS(ON)}	_	_	0.25	12	V_{GS} = -4.5 V , I_{D} =	-1.7A	
Forward Transconductance (Notes 9 & 10)	g _{fs}	_	4.4	_	S	V_{DS} = -15V, I_{D} =	-2.1A	
Diode Forward Voltage (Note 9)	V_{SD}	_	-0.85	-0.95	V	I _S = -2A, V _{GS} = 0V		
Reverse Recovery Time (Note 10)	t _{rr}	_	29.8	_	ns	I _S = -2.1A, di/dt= 100A/μs		
Reverse Recovery Charge (Note 10)	Q _{rr}	_	38.5		nC			
DYNAMIC CHARACTERISTICS (Note 10)								
Input Capacitance	C _{iss}	1	635	_	pF	.,	0) /	
Output Capacitance	Coss		52	_	pF	TVDS= -40V, VGS −f= 1MHz	V _{DS} = -40V, V _{GS} = 0V	
Reverse Transfer Capacitance	C _{rss}	_	42.5	_	pF	TE TIVIMZ		
Total Gate Charge (Note 11)	Q_{g}	_	9.6	_	nC	V _{GS} = -5V		
Total Gate Charge (Note 11)	Qg	_	18	_	nC	V _{DS} = -35V I _D = -2.1A		
Gate-Source Charge (Note 11)	Q_{gs}	_	1.77	_	nC			
Gate-Drain Charge (Note 11)	Q_{gd}	_	3.66	_	nC			
Turn-On Delay Time (Note 11)	t _{D(on)}	_	2.5	_	ns	V_{DD} = -35V, V_{GS} = -10V I_{D} = -1A, R_{G} \cong 6Ω		
Turn-On Rise Time (Note 11)	t _r		3.4		ns			
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	27.9		ns			
Turn-Off Fall Time (Note 11)	t _f	_	8	_	ns			

Notes:

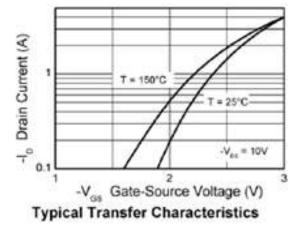
- 6. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as Note 6, except the device is measured at t ≤ 5 seconds.

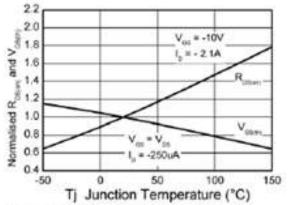
 8. Same as Note 6, except the device is pulsed with D= 0.05 and pulse width 10μs. The pulse current is limited by the maximum junction temperature.
- 9. Measured under pulsed conditions. Pulse width \leq 300 μ s; duty cycle \leq 2%.
- 10. For design aid only, not subject to production testing.
- 11. Switching characteristics are independent of operating junction temperatures.



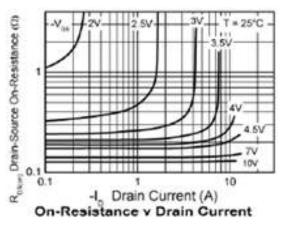


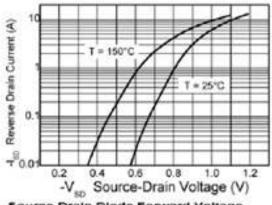




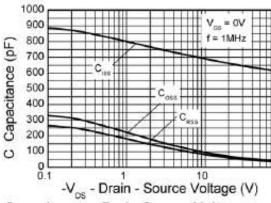


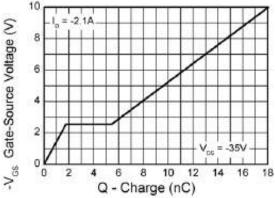
Normalised Curves v Temperature





Source-Drain Diode Forward Voltage





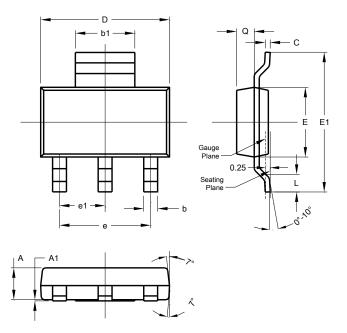
Capacitance v Drain-Source Voltage

Gate-Source Voltage v Gate Charge



Package Outline Dimensions

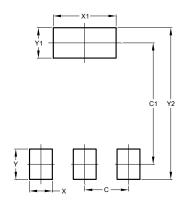
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
C	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
X	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		



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